VS-HFA16PA120C-N3

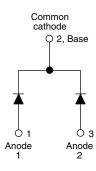
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A



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PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 8 A							
V _R	1200 V							
V _F at I _F	2.4 V							
t _{rr} typ.	28 ns							
T _J max.	150 °C							
Package	TO-247AC 3L							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -}{\sf JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the VS-HFA16PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I_	T _C = 100 °C	8						
per device	- I _F	$1_{\rm C} = 100$ C	16	А					
Single pulse forward current	I _{FSM}	t _p = 10 ms	130	A					
Maximum repetitive forward current	I _{FRM}		32						
Maximum power dissipation	PD	T _C = 25 °C	73.5	W					
	ΓD	T _C = 100 °C	29	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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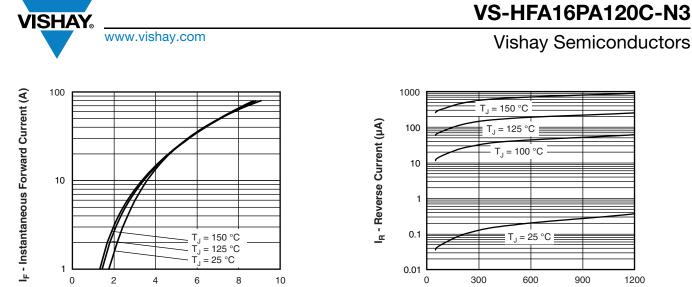
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ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage	V _{FM}	I _F = 8.0 A	-	2.6	3.3	V			
		I _F = 16 A	-	3.4	4.3				
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.31	10				
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA			
Junction capacitance	CT	V _R = 200 V	-	11	20	pF			
Series inductance	Ls	Measured lead to lead 5 mm from package	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 200$) A/µs, V _R = 30 V	-	28	-			
	t _{rr1}	T _J = 25 °C		-	63	95	ns		
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C	l _F = 8.0 A dl⊧/dt = 200 A/µs	-	4.5	8.0	A		
	I _{RRM2}	T _J = 125 °C		-	6.2	11			
	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{V}$	-	140	380			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880	no		
Peak rate of recovery current	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs		
during t _b	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	-					
Weight			-	6.0	-	g				
weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC 3L	HFA16PA120C							

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V_{FM} - Forward Voltage Drop (V)

Fig. 1 - Maximum Forward Voltage Drop Characteristics

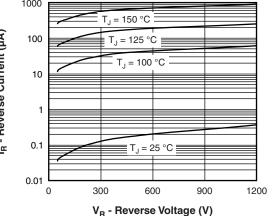


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

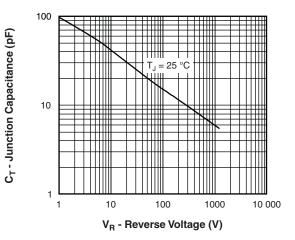


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

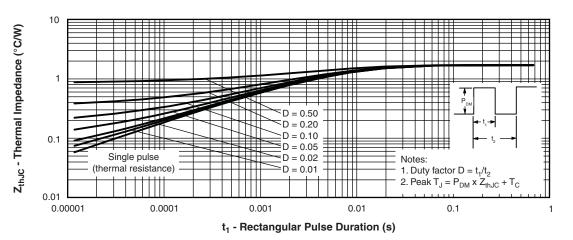


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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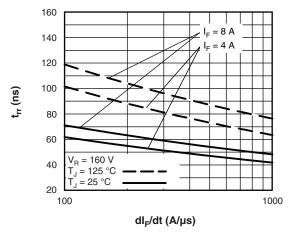


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

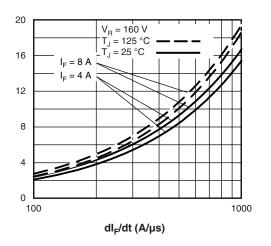
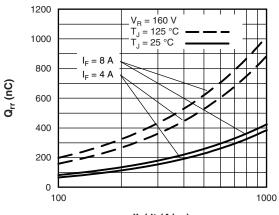


Fig. 6 - Typical Recovery Current vs. dl_F/dt







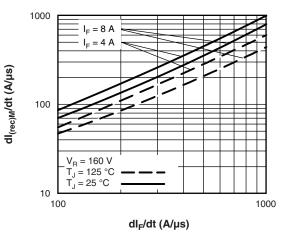


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

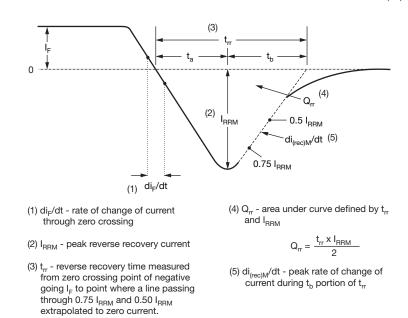


Fig. 9 - Reverse Recovery Waveform and Definitions

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I_{rr} (A)

VS-HFA16PA120C-N3

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	16	PA	120	С	-N3
		2	3	4	5	6	7	8
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	HEX Elec Cur PA Volt	KFRED [®] ctron irra rent rati = TO-2 ⁴ cage rati		= 16 A) pins) = 1200			
	7 -	Env	ironmer	n catho ntal digit en-free,	:	complia	int, and	totally

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16PA120C-N3	25	500	Antistatic plastic tube						

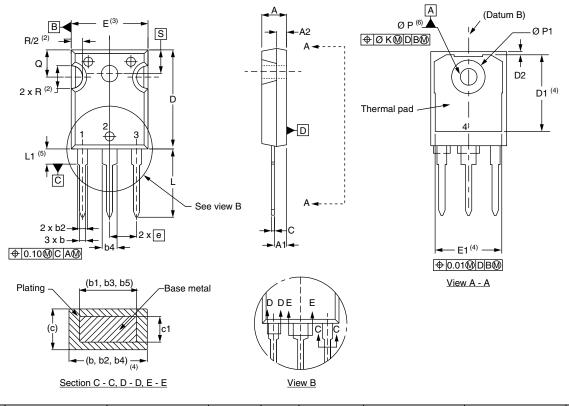
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					



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TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209		D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102		E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054		E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055		е	5.46	BSC	0.215	5 BSC	
b1	0.99	1.35	0.039	0.053		ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094		L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092		L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135		ØΡ	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133		Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035		Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033		R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3	S	5.51	BSC	0.217	' BSC	
D1	13.08	-	0.515	-	4						

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

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